



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

5 A

Features

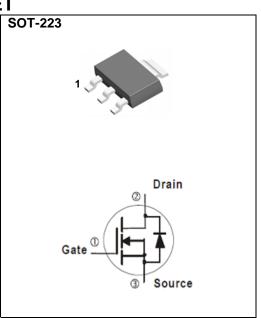
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@4A<115m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@2A<120m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SOT-223 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.043 ounces, 0.123 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	5	А	
	T _C =100°C		3.1		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	16		
Power Dissipation	T _C =25°C	ſ	5.2	10/	
	T _C =100°C	Po	2.1	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	3.5	_	
	T _A =70°C		2.8	Α	
Power Dissipation	T _A =25°C	Po	3.1	W	
	T _A =70°C		2		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	24	°C/W	
	Junction to Ambient	$R_{\theta JA}$	69.4		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA V _{DS} =V _{GS} , I _D =250uA	100	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$		1	1.76	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =4A	-	92	115	mΩ	
		V _{GS} =4.5V,I _D =2A	-	95	120		
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Q_g	V _{DS} =50V, I _D =2A, V _{GS} =10V ^(Note 1,2)	-	20	-	nC	
Gate-Source Charge	Q_gs		-	3.2	-		
Gate-Drain Charge	Q_{gd}		-	3.6	-		
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	1413	-	pF	
Output Capacitance	Coss		-	60	-		
Reverse Transfer Capacitance	Crss	I= IIVII IZ	-	34	-		
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =1A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	18	-		
Turn-On Rise Time	t _r		-	4.3	-	ns	
Turn-Off Delay Time	td _(off)		-	41	-		
Turn-Off Fall Time	t _f	N _G =3.312	-	4.2	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	I.				5	Α	
Diode Forward Current	I _S		-	_	3	^	
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.73	1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

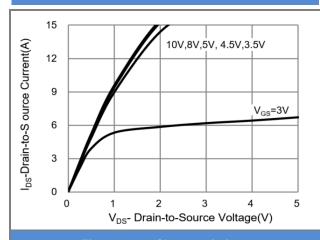


Fig.1 Output Characteristics

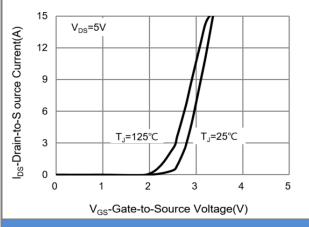


Fig.2 Transfer Characteristics

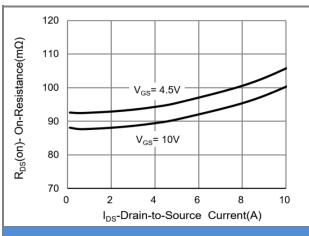


Fig.3 On-Resistance vs. Drain Current

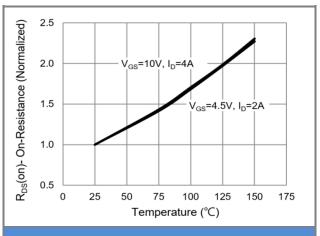


Fig.4 On-Resistance vs. Junction temperature

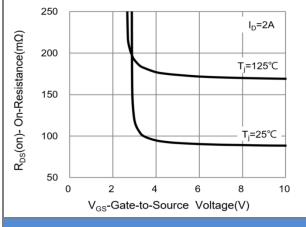


Fig.5 On-Resistance Variation with V_{GS}

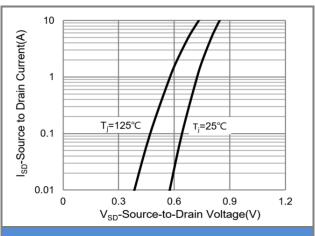


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

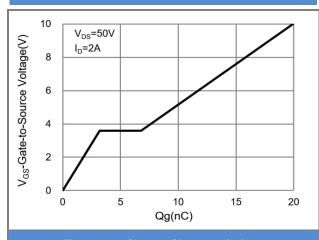


Fig.7 Gate-Charge Characteristics

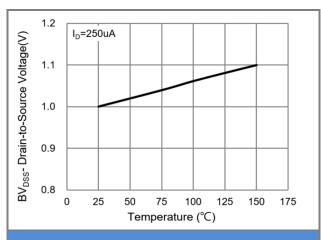


Fig.8 Breakdown Voltage Variation vs. Temperature

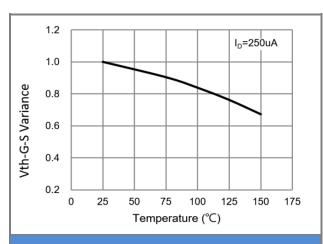


Fig.9 Threshold Voltage Variation with Temperature

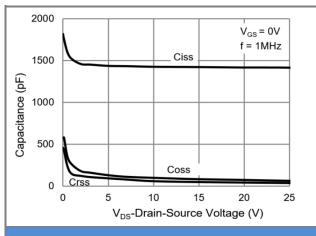


Fig.10 Capacitance vs. Drain-Source Voltage

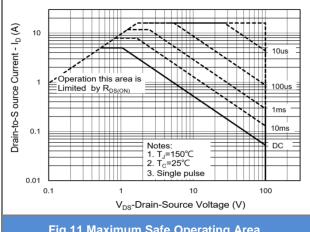


Fig.11 Maximum Safe Operating Area

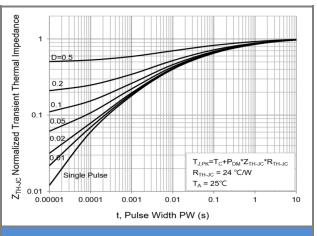
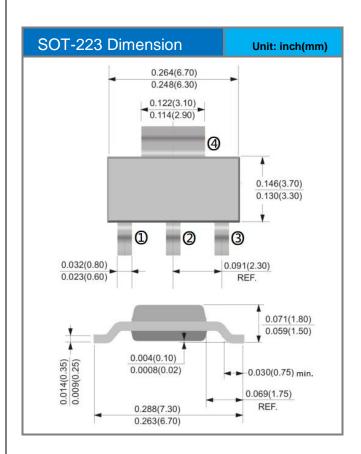


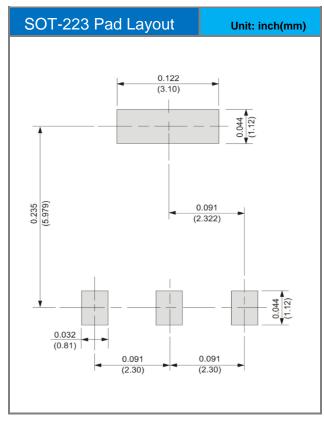
Fig.12 Normalized Transient Thermal Impedance





Packaging Information & Mounting Pad Layout









Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJW5N10A_R2_00001	SOT-223	2,500pcs / 13" reel	W5N10A	Halogen free





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